

N-channel 800 V, 0.19 Ω typ., 19.5 A SuperMESH™5 Power MOSFET
in D²PAK, TO-220FP, TO-220 and TO-247 packages

Datasheet – production data

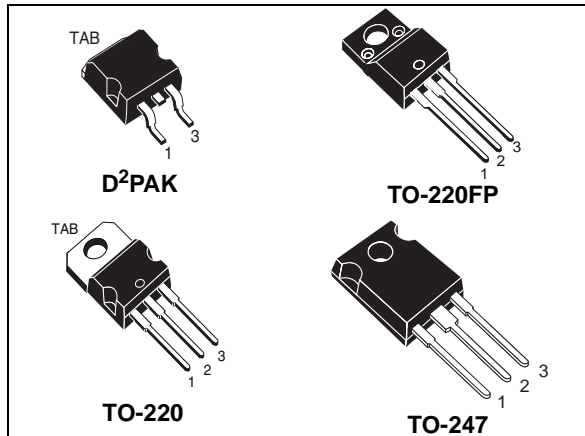
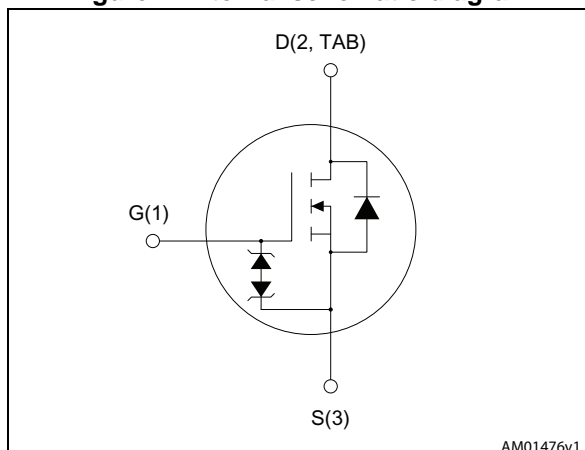


Figure 1. Internal schematic diagram



Features

Order codes	$V_{DS} @ T_{Jmax}$	$R_{DS(on) max}$	I_D	P_{TOT}
STB25N80K5	800 V	< 0.260 Ω	19.5 A	250 W
STF25N80K5				40 W
STP25N80K5				250 W
STW25N80K5				

- TO-220 worldwide best $R_{DS(on)}$
- Worldwide best FOM (figure of merit)
- Ultra low gate charge
- 100% avalanche tested
- Zener-protected

Applications

- Switching applications

Description

These N-channel Zener-protected Power MOSFET are designed using ST's revolutionary avalanche-rugged very high voltage SuperMESH™ 5 technology, based on an innovative proprietary vertical structure. The result is a dramatic reduction in on-resistance, and ultra-low gate charge for applications which require superior power density and high efficiency.

Table 1. Device summary

Order codes	Marking	Package	Packaging
STB25N80K5	25N80K5	D ² PAK	Tape and reel
STF25N80K5		TO-220FP	Tube
STP25N80K5		TO-220	
STW25N80K5		TO-247	

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value		Unit
		D ² PAK, TO-220, TO-247	TO-220FP	
V _{GS}	Gate- source voltage	± 30		V
I _D	Drain current (continuous) at T _C = 25 °C	19.5	19.5 ⁽¹⁾	A
I _D	Drain current (continuous) at T _C = 100 °C	12.3	12.3 ⁽¹⁾	A
I _{DM} ⁽²⁾	Drain current (pulsed)	78	78 ⁽¹⁾	A
P _{TOT}	Total dissipation at T _C = 25 °C	250	40	W
I _{AR}	Max current during repetitive or single pulse avalanche (pulse width limited by T _{jmax})	6.5		A
E _{AS}	Single pulse avalanche energy (starting T _J = 25 °C, I _D =I _{AS} , V _{DD} = 50 V)	200		mJ
V _{iso}	Insulation withstand voltage (RMS) from all three leads to external heat sink (t=1 s; T _C =25 °C)		2500	V
dv/dt ⁽³⁾	Peak diode recovery voltage slope	6		V/ns
T _j T _{stg}	Operating junction temperature Storage temperature	-55 to 150		°C

- Limited by package.
- Pulse width limited by safe operating area.
- $I_{SD} \leq 19.5$ A, $di/dt \leq 100$ A/ μ s, $V_{Peak} \leq V_{(BR)DSS}$

Table 3. Thermal data

Symbol	Parameter	Value				Unit
		TO-220	TO-247	D ² PAK	TO-220FP	
R _{thj-case}	Thermal resistance junction-case max	0.5			3.1	°C/W
R _{thj-amb}	Thermal resistance junction-amb max	62.5	50		62.5	
R _{thj-pcb} ⁽¹⁾	Thermal resistance junction-pcb max			30		

- When mounted on 1inch² FR-4 board, 2 oz Cu.

2 Electrical characteristics

($T_{CASE} = 25\text{ °C}$ unless otherwise specified).

Table 4. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage ($V_{GS} = 0$)	$I_D = 1\text{ mA}$	800			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = 800\text{ V}$ $V_{DS} = 800\text{ V}, T_C = 125\text{ °C}$			1 50	μA μA
I_{GSS}	Gate body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20\text{ V}$			± 10	μA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 100\text{ }\mu\text{A}$	3	4	5	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10\text{ V}, I_D = 10\text{ A}$		0.19	0.260	Ω

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 100\text{ V}, f = 1\text{ MHz}, V_{GS} = 0$	-	1600	-	pF
C_{oss}	Output capacitance		-	130	-	pF
C_{rss}	Reverse transfer capacitance		-	2	-	pF
$C_{o(tr)}^{(1)}$	Equivalent capacitance time related	$V_{GS} = 0, V_{DS} = 0\text{ to }640\text{ V}$	-	185	-	pF
$C_{o(er)}^{(2)}$	Equivalent capacitance energy related		-	300	-	pF
R_G	Intrinsic gate resistance	$f = 1\text{ MHz open drain}$	-	4	-	Ω
Q_g	Total gate charge	$V_{DD} = 640\text{ V}, I_D = 19.5\text{ A}$ $V_{GS} = 10\text{ V}$ (see Figure 19)	-	40	-	nC
Q_{gs}	Gate-source charge		-	10		nC
Q_{gd}	Gate-drain charge		-	25		nC

1. Time related is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}
2. Energy related is defined as a constant equivalent capacitance giving the same stored energy as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 400\text{ V}$, $I_D = 10\text{ A}$, $R_G = 4.7\ \Omega$, $V_{GS} = 10\text{ V}$ (see Figure 21)	-	25	-	ns
t_r	Rise time		-	13	-	ns
$t_{d(off)}$	Turn-off delay time		-	60	-	ns
t_f	Fall time		-	15	-	ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		19.5	A
I_{SDM}	Source-drain current (pulsed)		-		78	A
$V_{SD}^{(1)}$	Forward on voltage	$I_{SD} = 19.5\text{ A}$, $V_{GS} = 0$	-		1.5	V
t_{rr}	Reverse recovery time	$I_{SD} = 19.5\text{ A}$, $V_{DD} = 60\text{ V}$ $di/dt = 100\text{ A}/\mu\text{s}$, (see Figure 20)	-	515		ns
Q_{rr}	Reverse recovery charge		-	11		μC
I_{RRM}	Reverse recovery current		-	43.2		A
t_{rr}	Reverse recovery time	$I_{SD} = 19.5\text{ A}$, $V_{DD} = 60\text{ V}$ $di/dt = 100\text{ A}/\mu\text{s}$, $T_J = 150\text{ }^\circ\text{C}$ (see Figure 20)	-	615		ns
Q_{rr}	Reverse recovery charge		-	13		μC
I_{RRM}	Reverse recovery current		-	43		A

1. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

Table 8. Gate-source Zener diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)GSO}$	Gate-source breakdown voltage	$I_{GS} = \pm 1\text{ mA}$, $I_D = 0$	30	-	-	V

The built-in back-to-back Zener diodes have been specifically designed to enhance not only the device's ESD capability, but also to make them capable of safely absorbing any voltage transients that may occasionally be applied from gate to source. In this respect, the Zener voltage is appropriate to achieve efficient and cost-effective protection of device integrity. The integrated Zener diodes thus eliminate the need for external components.

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area for D²PAK

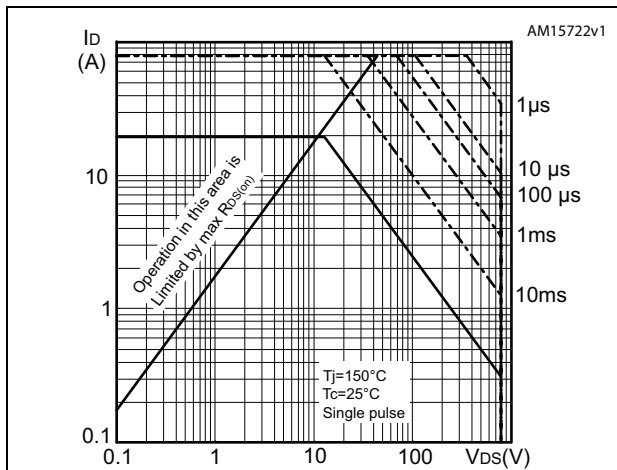


Figure 3. Thermal impedance for D²PAK and TO-220

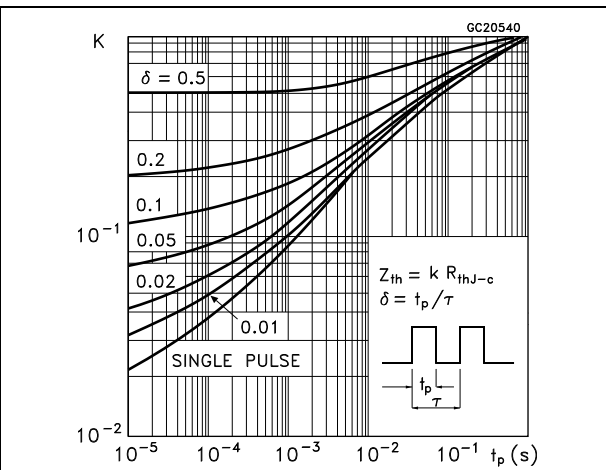


Figure 4. Safe operating area for TO-220FP

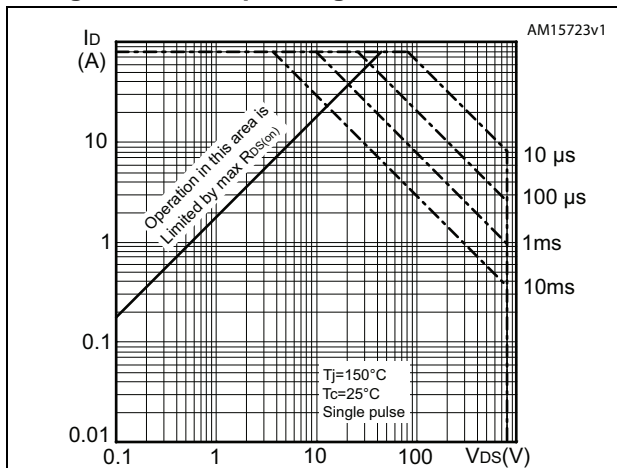


Figure 5. Thermal impedance for TO-220FP

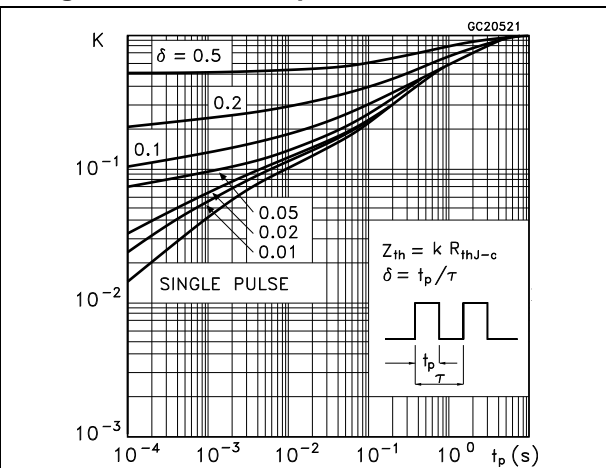


Figure 6. Safe operating area for TO-220

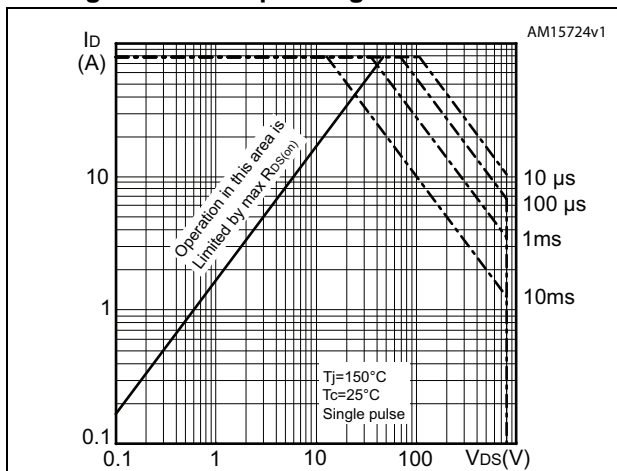


Figure 7. Normalized B_{VDSS} vs temperature

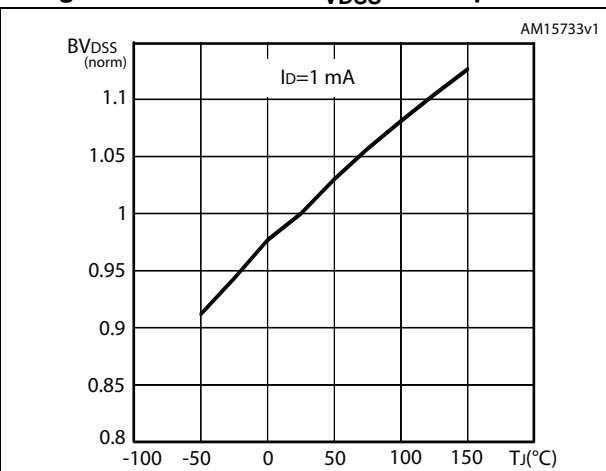


Figure 8. Safe operating area for TO-247

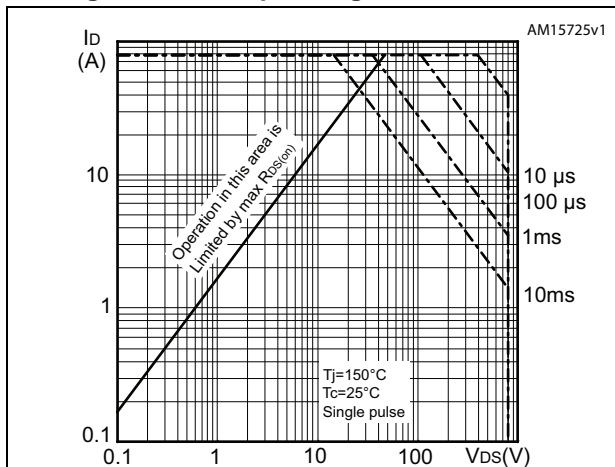


Figure 9. Thermal impedance for TO-247

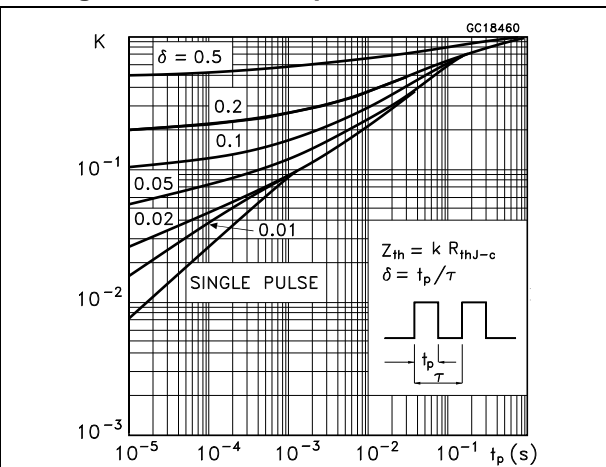


Figure 10. Output characteristics

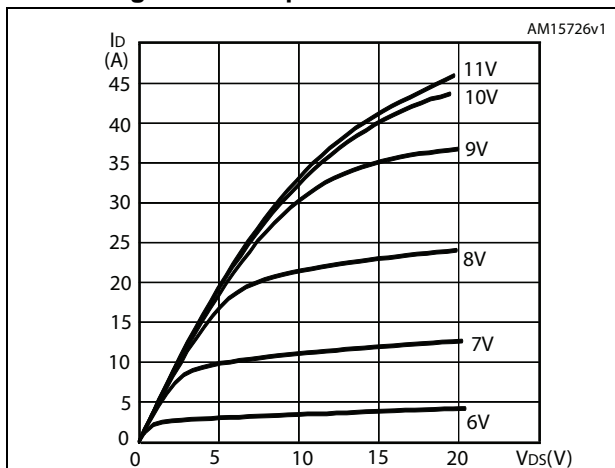


Figure 11. Transfer characteristics

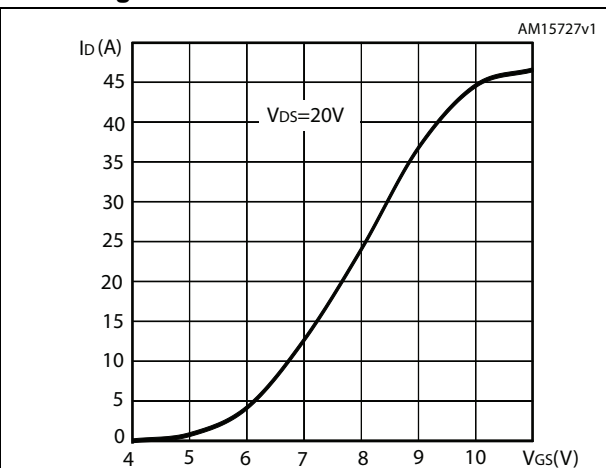


Figure 12. Static drain-source on-resistance

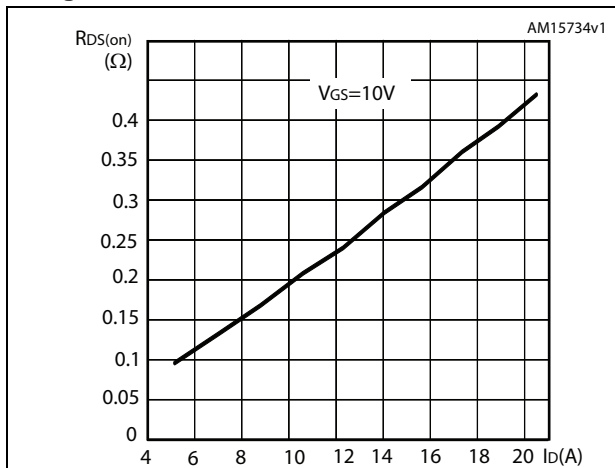


Figure 13. Gate charge vs gate-source voltage

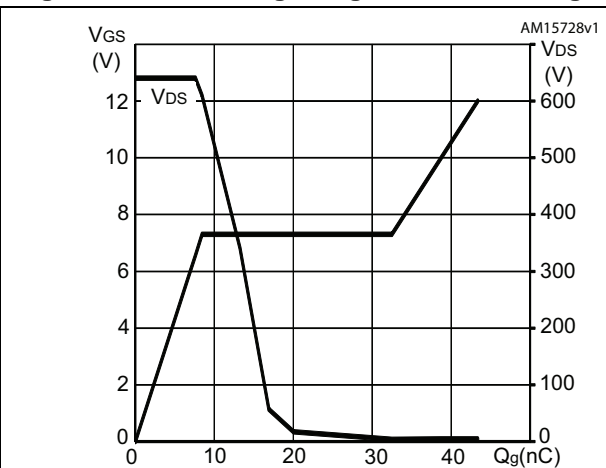


Figure 14. Capacitance variations

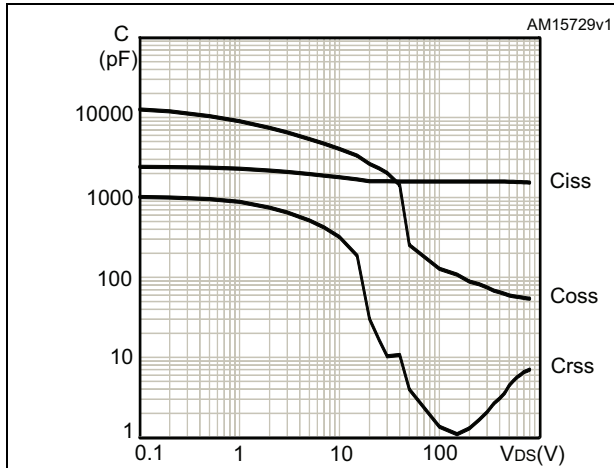


Figure 15. Output capacitance stored energy

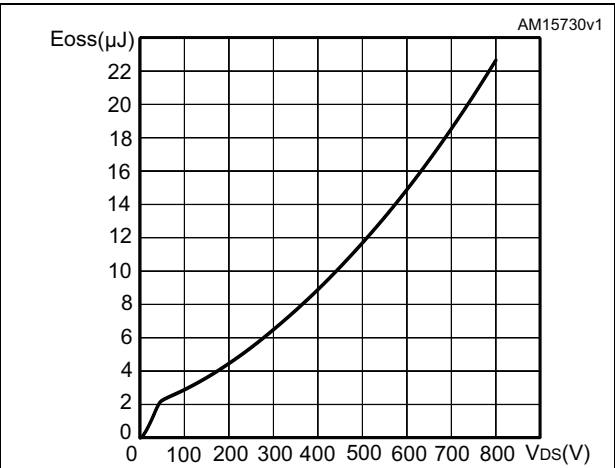


Figure 16. Normalized on-resistance vs temperature

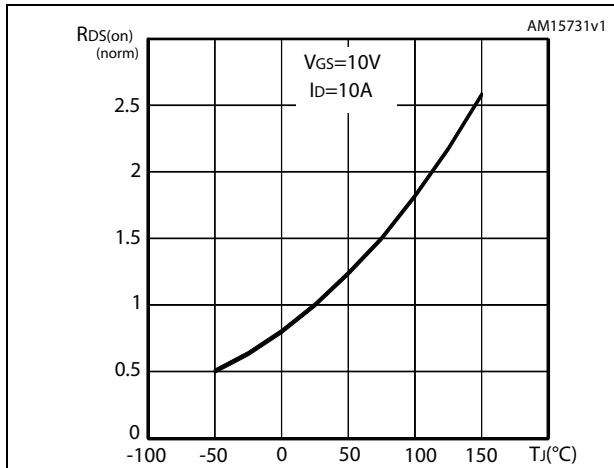
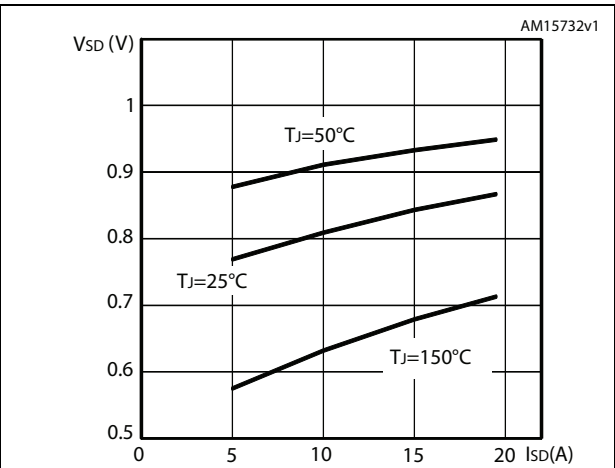


Figure 17. Source-drain diode forward characteristics



3 Test circuits

Figure 18. Switching times test circuit for resistive load



Figure 19. Gate charge test circuit

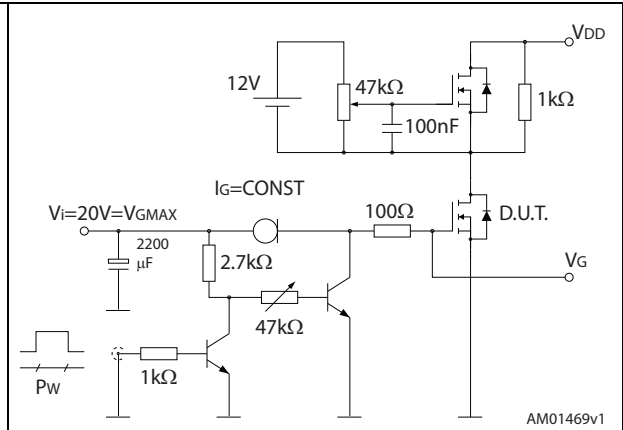


Figure 20. Test circuit for inductive load switching and diode recovery times

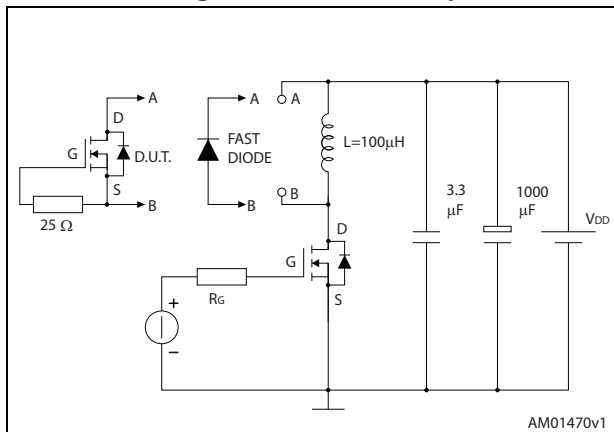


Figure 21. Unclamped inductive load test circuit

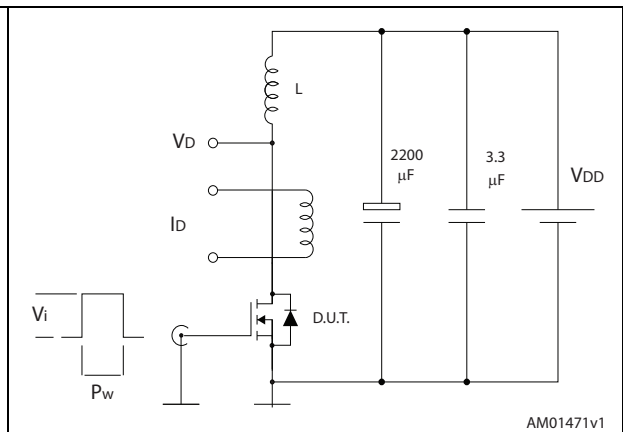


Figure 22. Unclamped inductive waveform

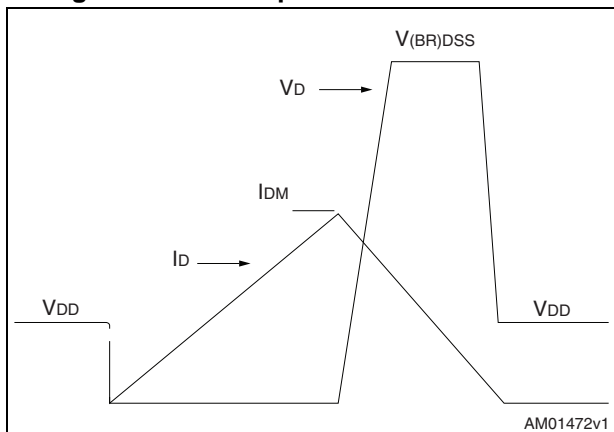
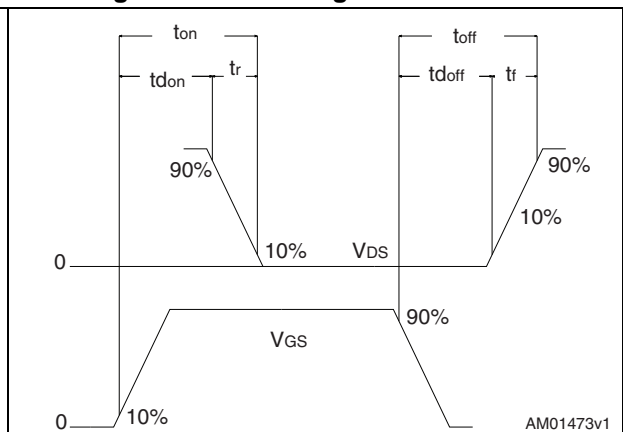


Figure 23. Switching time waveform



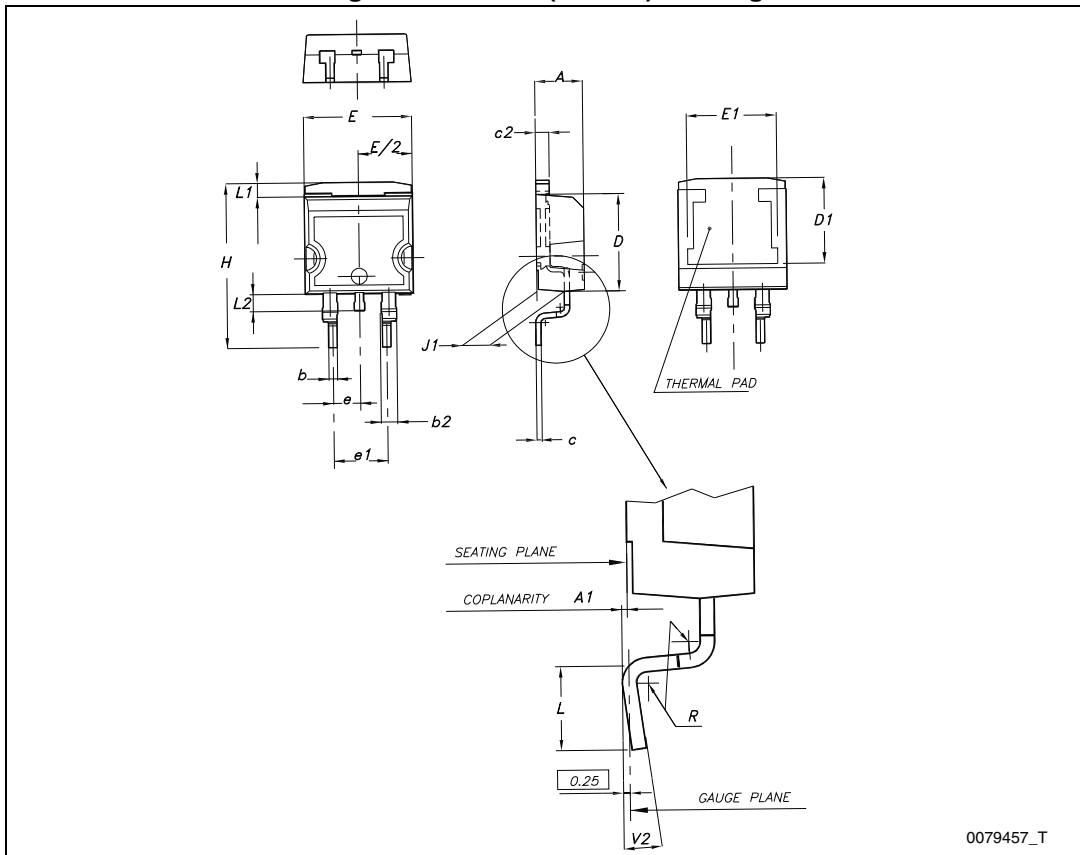
4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

Table 9. D²PAK (TO-263) mechanical data

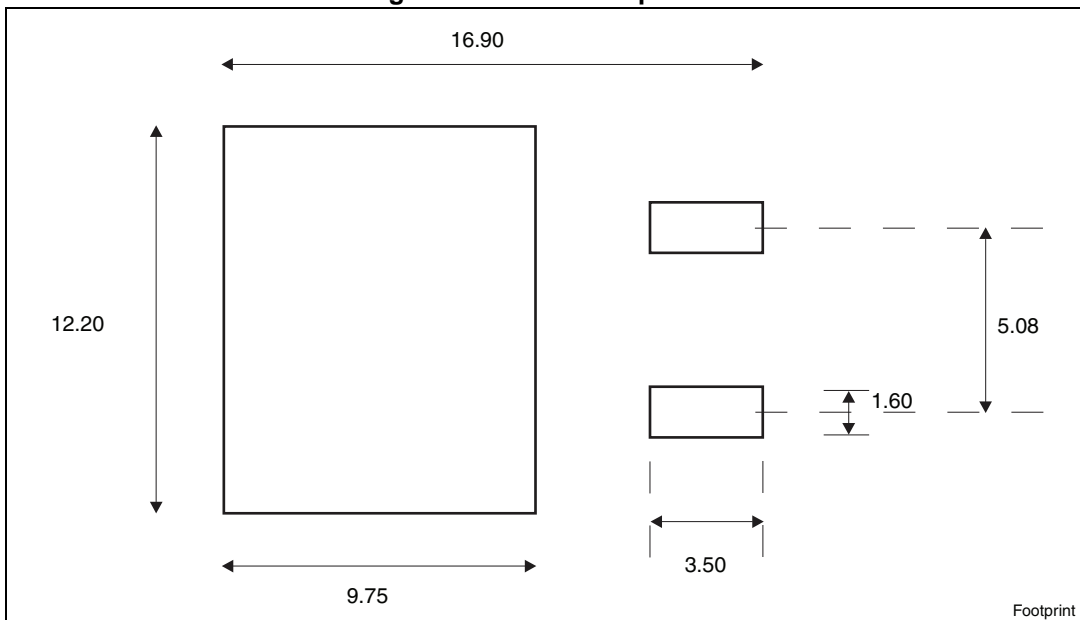
Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
A1	0.03		0.23
b	0.70		0.93
b2	1.14		1.70
c	0.45		0.60
c2	1.23		1.36
D	8.95		9.35
D1	7.50		
E	10		10.40
E1	8.50		
e		2.54	
e1	4.88		5.28
H	15		15.85
J1	2.49		2.69
L	2.29		2.79
L1	1.27		1.40
L2	1.30		1.75
R		0.4	
V2	0°		8°

Figure 24. D²PAK (TO-263) drawing



0079457_T

Figure 25. D²PAK footprint^(a)

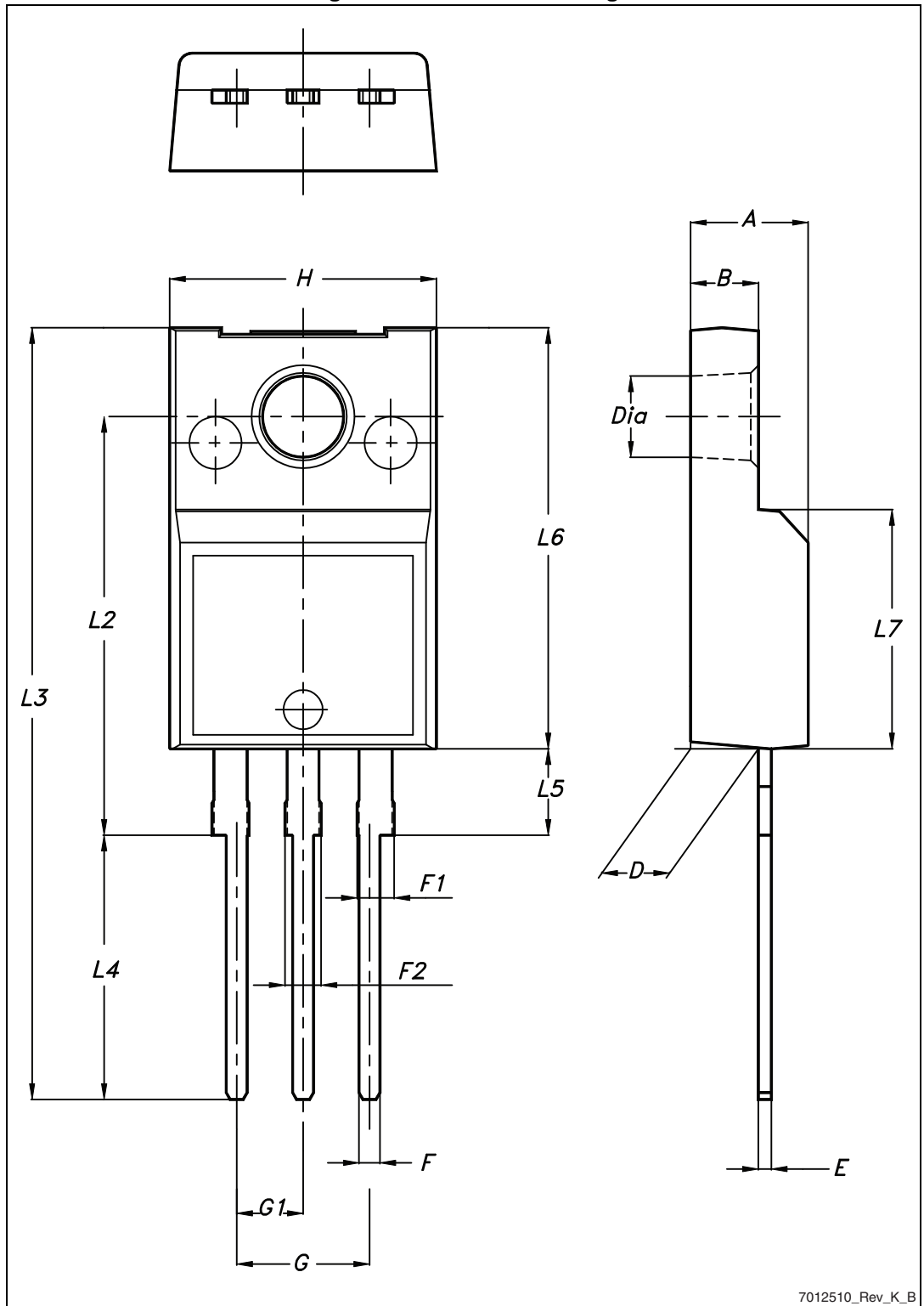


a. All dimension are in millimeters

Table 10. TO-220FP mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.4		4.6
B	2.5		2.7
D	2.5		2.75
E	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.2
G1	2.4		2.7
H	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Dia	3		3.2

Figure 26. TO-220FP drawing



7012510_Rev_K_B

Table 11. TO-220 type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
ØP	3.75		3.85
Q	2.65		2.95

Figure 27. TO-220 type A drawing

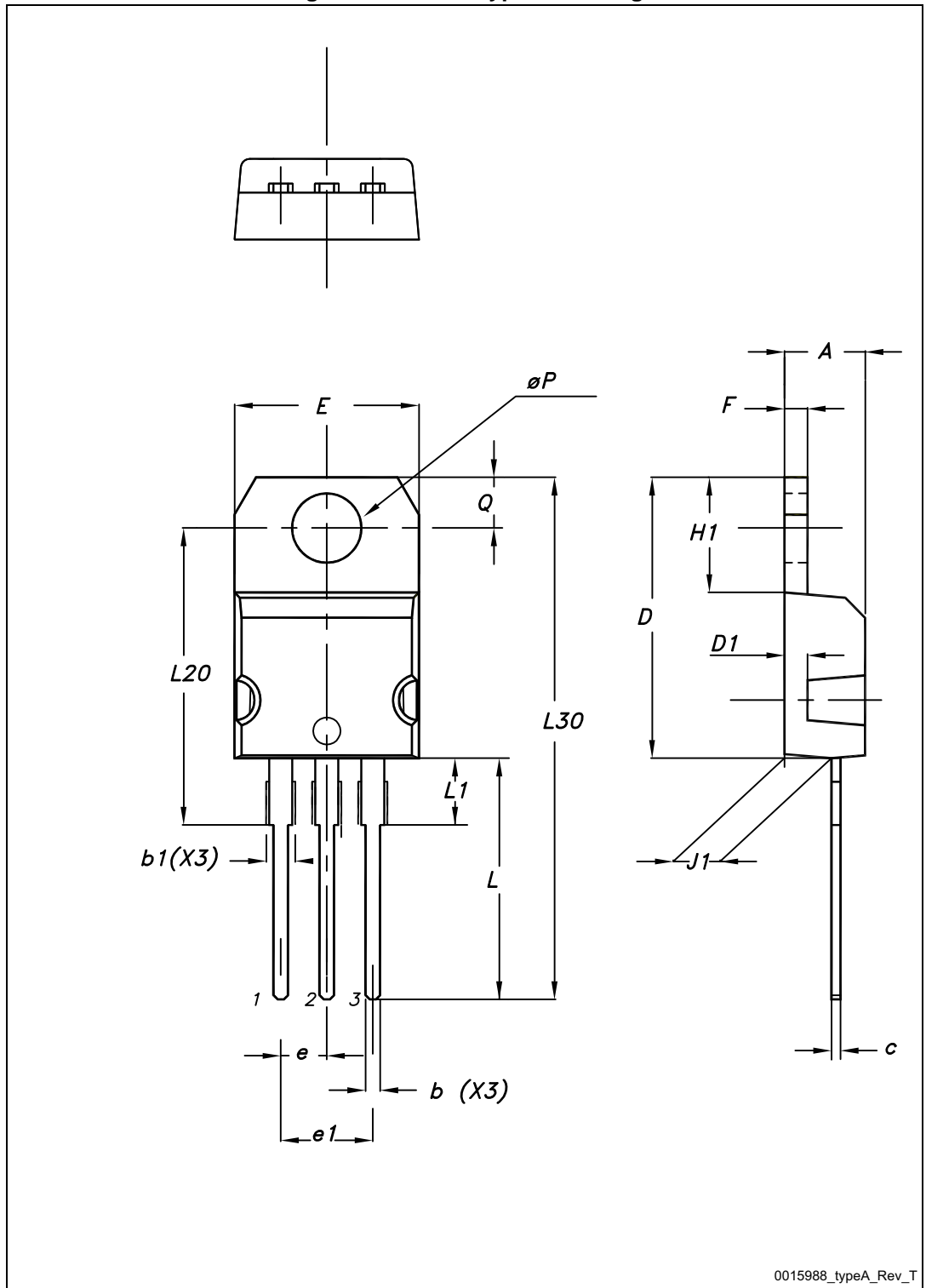
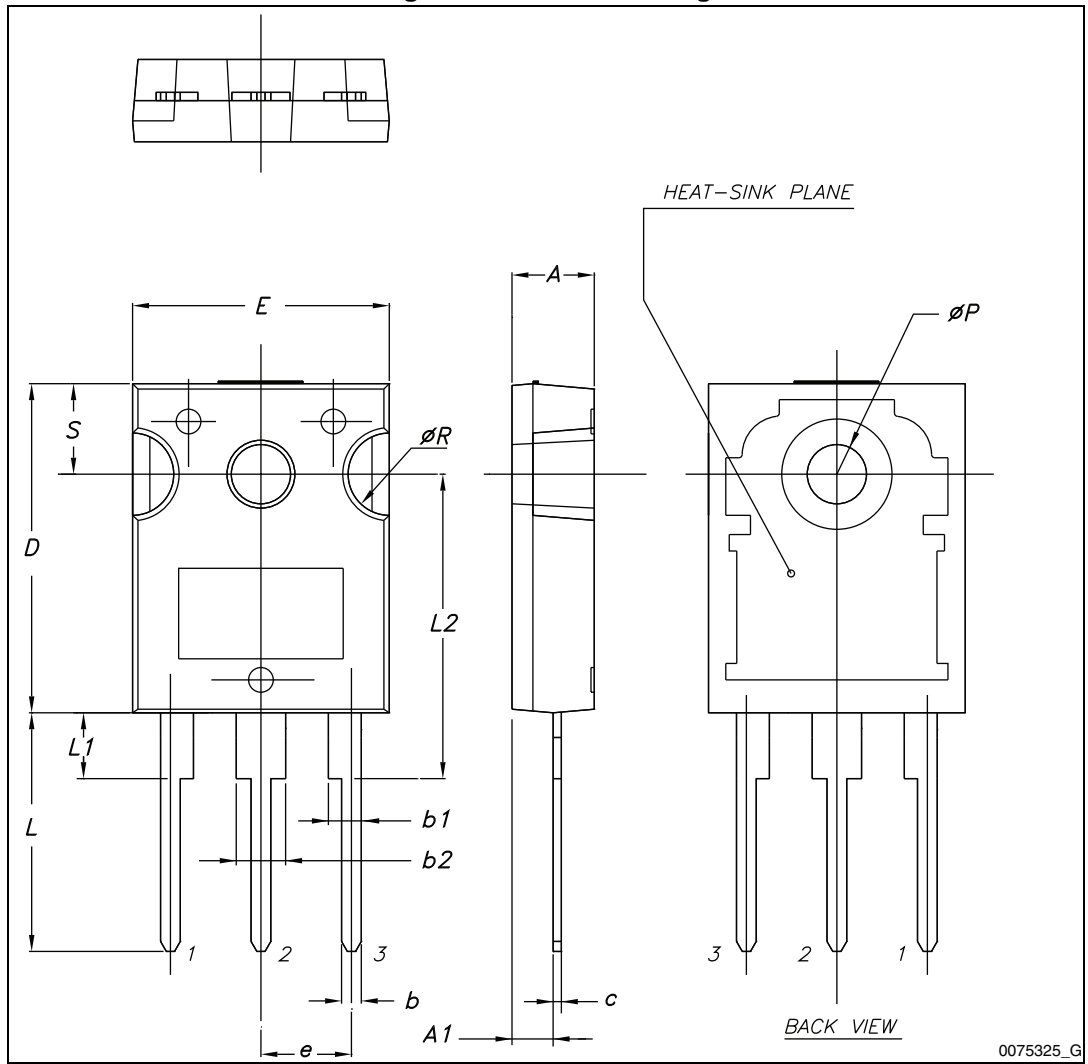


Table 12. TO-247 mechanical data

Dim.	mm.		
	Min.	Typ.	Max.
A	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
c	0.40		0.80
D	19.85		20.15
E	15.45		15.75
e	5.30	5.45	5.60
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
ØP	3.55		3.65
ØR	4.50		5.50
S	5.30	5.50	5.70

Figure 28. TO-247 drawing



5 Packaging information

Table 13. D²PAK (TO-263) tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	10.5	10.7	A		330
B0	15.7	15.9	B	1.5	
D	1.5	1.6	C	12.8	13.2
D1	1.59	1.61	D	20.2	
E	1.65	1.85	G	24.4	26.4
F	11.4	11.6	N	100	
K0	4.8	5.0	T		30.4
P0	3.9	4.1			
P1	11.9	12.1		Base qty	1000
P2	1.9	2.1		Bulk qty	1000
R	50				
T	0.25	0.35			
W	23.7	24.3			

Figure 29. Tape

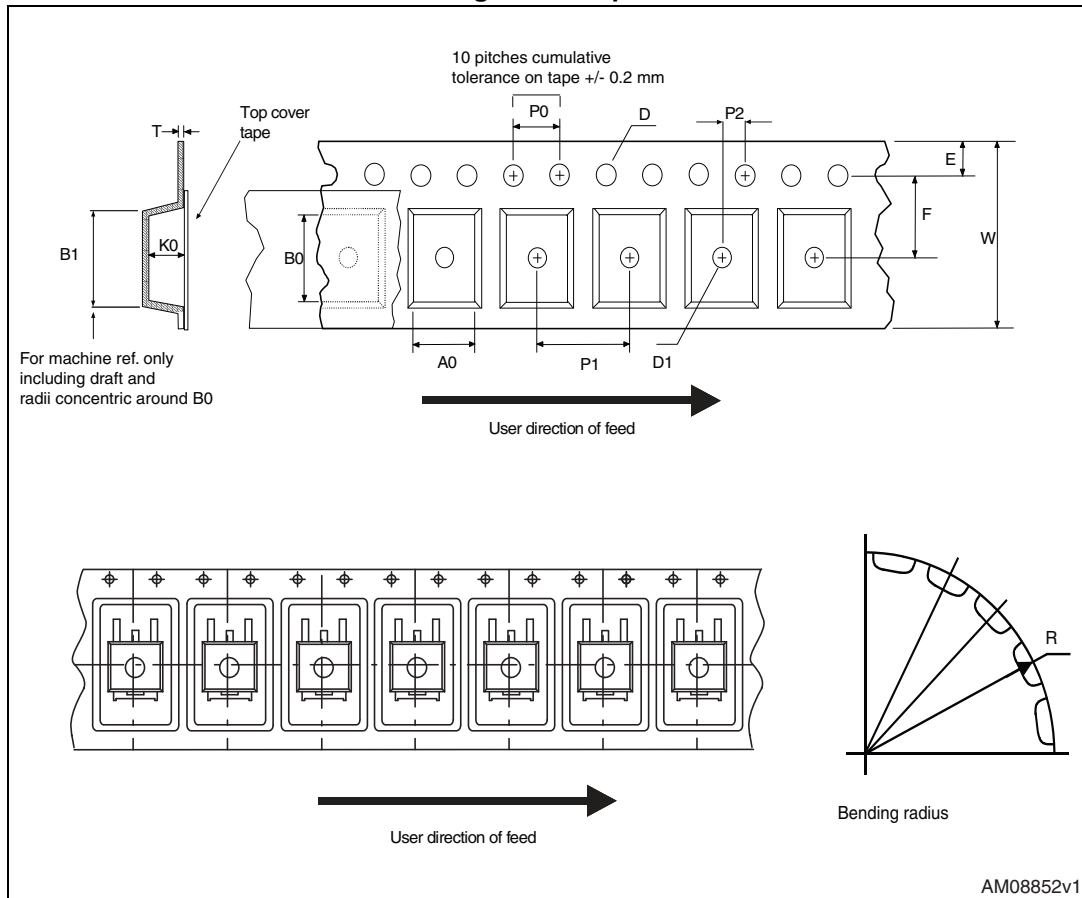
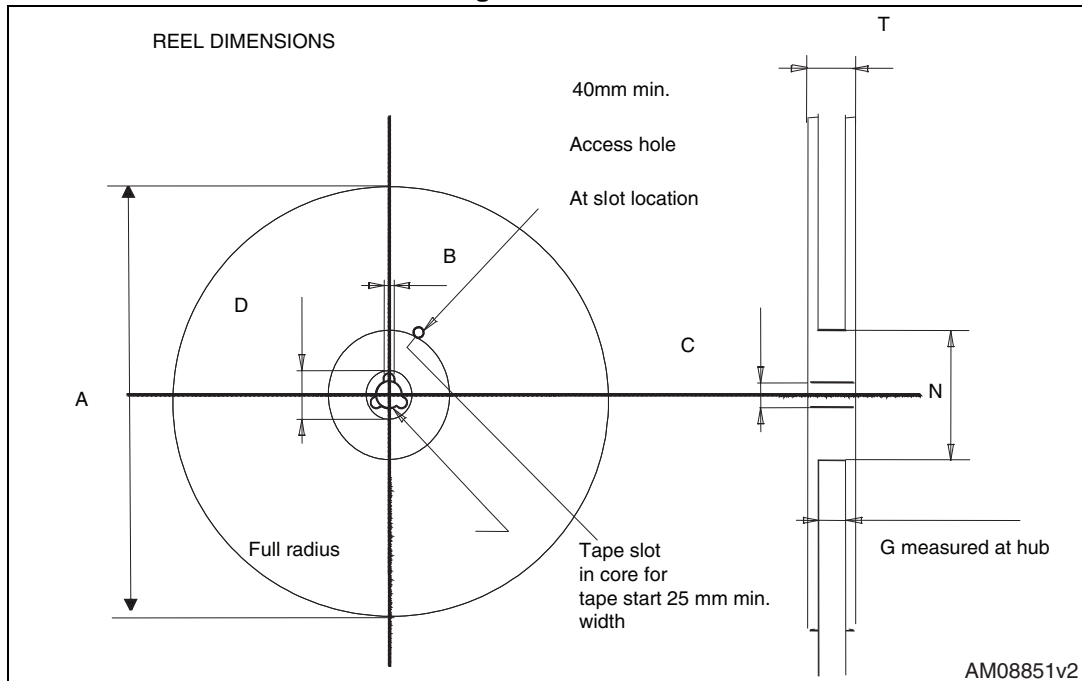


Figure 30. Reel



6 Revision history

Table 14. Document revision history

Date	Revision	Changes
17-Jul-2012	1	First release.
04-Jun-2013	2	<ul style="list-style-type: none">– Modified: I_{AR}, E_{AS}, dv/dt on Table 2, $R_{DS(on)}$ value on Table 4, entire values on Table 5, 6 and 7– Updated: Section 4: Package mechanical data– Minor text changes– Updated: Table 11 and Figure 27– Document status promoted from preliminary data to production data

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